

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02580F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

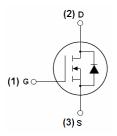
- $V_{DS} = 250V, I_{D} = 80A$ $R_{DS(ON)} < 18.5 m\Omega @ V_{GS} = 10V$
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

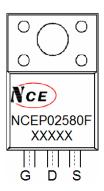
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220F top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02580F	NCEP02580F	TO-220F-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	80	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	56.6	А
Pulsed Drain Current	I _{DM}	320	А
Maximum Power Dissipation	P _D	50	W
Derating factor		3	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	1200	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$ C



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NCEP02580F

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	ReJC	0.33	°C/W	Ī
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	16	18.5	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =40A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -425\/\/ -0\/	-	5400	-	PF
Output Capacitance	Coss	V_{DS} =125V, V_{GS} =0V, F=1.0MHz	-	329	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0lvln2	-	12	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	t _r	V_{DD} =125 V , I_{D} =40 A	-	26	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10V, R_{G} =4.7 Ω	-	41	-	nS
Turn-Off Fall Time	t _f		-	11	-	nS
Total Gate Charge	Qg	\/ -405\/ -404	-	76.7		nC
Gate-Source Charge	Q _{gs}	V_{DS} =125V, I_{D} =40A, V_{GS} =10V	-	22.7		nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	20		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =80A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	80	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = 40$	-	140		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	_	600		nC

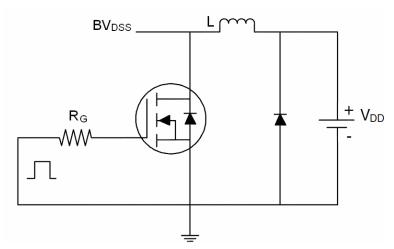
Notes:

- ${\it 1. Repetitive Rating: Pulse width limited by maximum junction temperature.}\\$
- 2. Surface Mounted on FR4 Board, t \leq 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω

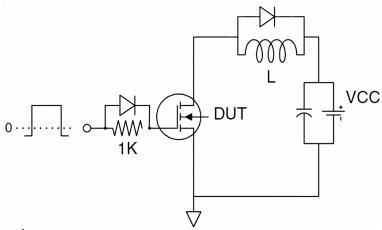


Test Circuit

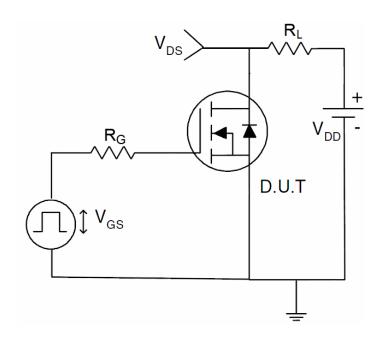
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







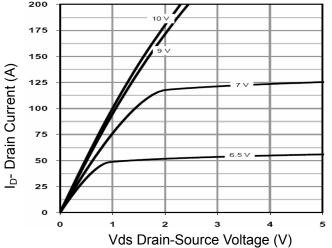


Figure 1 Output Characteristics

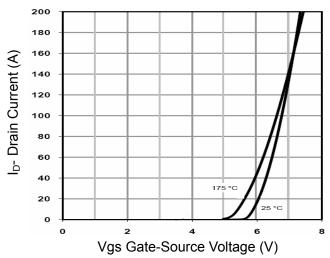


Figure 2 Transfer Characteristics

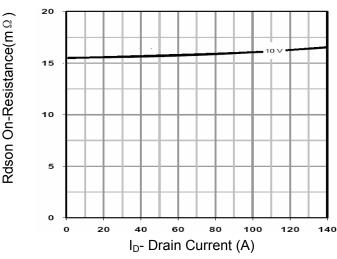


Figure 3 Rdson- Drain Current

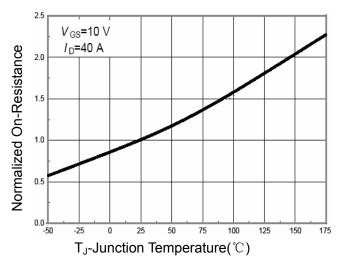


Figure 4 Rdson-JunctionTemperature

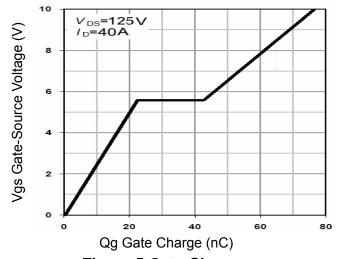


Figure 5 Gate Charge

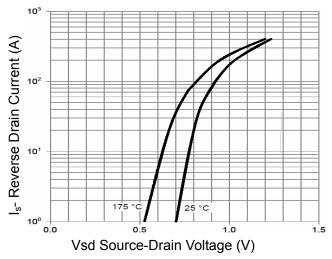
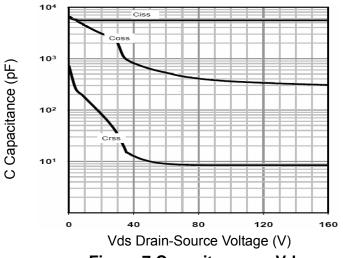


Figure 6 Source- Drain Diode Forward

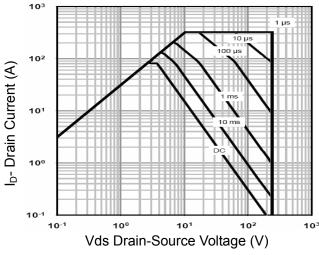




(M) uoited 40 0 0 50 100 150 200 T_J-Junction Temperature (°C)

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



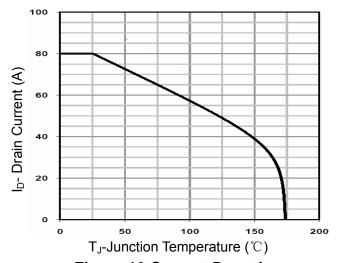
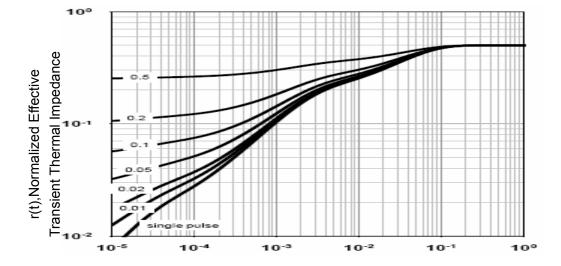


Figure 8 Safe Operation Area

Figure 10 Current De-rating

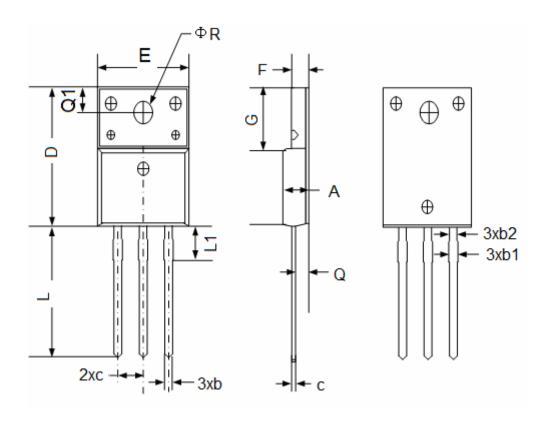


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220F Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	4.50	4.83	0. 18	0. 19		
b	0.70	0.91	0.03	0.04		
b1	1.20	1.47	0.05	0.06		
b2	1.10	1.38	0.04	0.05		
С	0.45	0.63	0. 02	0.02		
D	15.67	16.07	0.62	0.63		
е	2.54	2.54 BSC		0.10 BSC		
Е	9.96	10.36	0. 39	0.41		
F	2.34	2.74	0.09	0. 11		
G	6.48	6.90	0. 26	0. 27		
L	12.68	13.30	0. 50	0. 52		
L1	3.13	3.50	0. 12	0.14		
Q	2.56	2.93	0. 10	0. 12		
Q1	3.20	3.40	0. 13	0. 13		
ΦR	3.08	3.28	0. 12	0. 13		

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